Features

- For Sensitive ESD Protection
- Excellent Clamping Capability
- Low Clamping Voltage
- Moisture Sensitivity Level 1
- Halogen Free. “Green” Device (Note 1)
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

ESD Protection Device

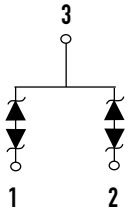
Maximum Ratings

IEC61000-4-2 (ESD)	Air	±30KV
	Contact	±30KV
Peak Pulse Current (8/20μs) Pin1,2 to Pin3	I_{PP}	12A
Peak Pulse Current (8/20μs) Pin3 to Pin1,2	I_{PP}	17A
Peak Pulse Power (8/20μs)(Note2)	P_{PK}	240W
Operating Junction Temperature Range	T_J	-55°C to +125°C
Storage Temperature Range	T_{STG}	-55°C to +150°C

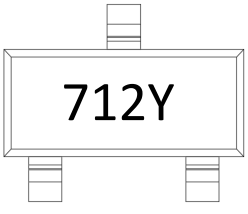
Note :

1. Halogen free "Green” products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
2. Non-repetitive current pulse 8/20 μs exponential decay waveform according to IEC61000-4-5.

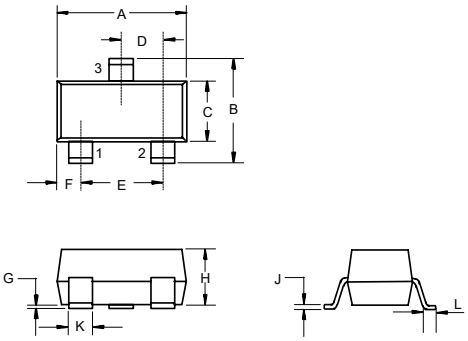
Internal Structure



Marking Code

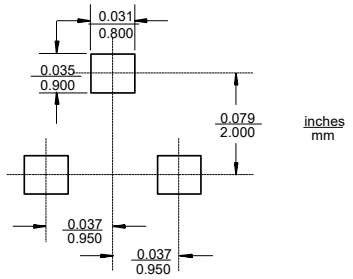


SOT-23

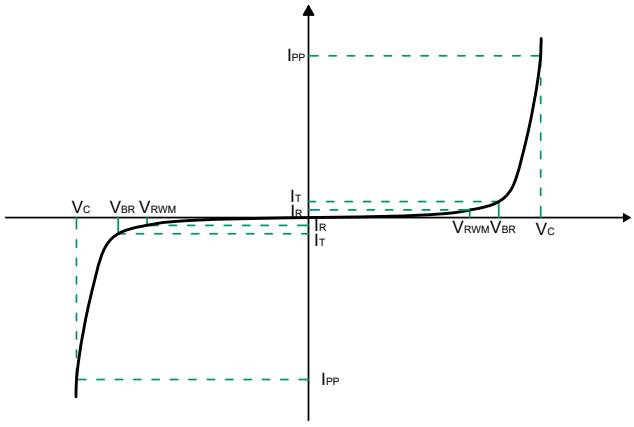


DIMENSIONS					
DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.110	0.120	2.80	3.04	
B	0.083	0.104	2.10	2.64	
C	0.047	0.055	1.20	1.40	
D	0.034	0.041	0.85	1.05	
E	0.067	0.083	1.70	2.10	
F	0.018	0.024	0.45	0.60	
G	0.0004	0.006	0.01	0.15	
H	0.035	0.043	0.90	1.10	
J	0.003	0.007	0.08	0.18	
K	0.012	0.020	0.30	0.51	
L	0.007	0.020	0.20	0.50	

Suggested Solder Pad Layout



Symbol	Parameter
V_{RWM}	Peak Reverse Working Voltage
I_R	Reverse Leakage Current @ VRWM
V_{BR}	Breakdown Voltage @ IT
IT	Test Current
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage @ IPP
P_{PK}	Peak Pulse Power
C_J	Junction Capacitance



Electrical Characteristics @ 25°C (Unless Otherwise Specified)

Pin1,2 to Pin3						
Parameter	**Symbol**	**Conditions**	**Min.**	**Typ.**	**Max.**	**Units**
Reverse Working Voltage	V_{RWM}				12	V
Reverse Breakdown Voltage	V_{BR}	I_T=1mA	13.3			V
Reverse Leakage Current	I_R	V_{RWM}=12V			0.5	μA
Clamping Voltage Note1	V_C	I_{PP}=1A, t_P=8/20μs			17	V
Clamping Voltage Note1	V_C	I_{PP}=12A, t_P=8/20μs			20	V
Junction Capacitance	C_J	V_R=0V, f=1MHz		25		pF
Dynamic Resistance Note2	R_{DYN}	TLP, t_P=100ns		0.1		Ω
Pin3 to Pin1,2						
Parameter	**Symbol**	**Conditions**	**Min.**	**Typ.**	**Max.**	**Units**
Reverse Working Voltage	V_{RWM}				7	V
Reverse Breakdown Voltage	V_{BR}	I_T=1mA	7.5			V
Reverse Leakage Current	I_R	V_{RWM}=7V			0.5	μA
Clamping Voltage Note1	V_C	I_{PP}=1A, t_P=8/20μs			11	V
Clamping Voltage Note1	V_C	I_{PP}=17A, t_P=8/20μs			14.5	V
Junction Capacitance	C_J	V_R=0V, f=1MHz		25		pF
Dynamic Resistance Note2	R_{DYN}	TLP, t_P=100ns		0.1		Ω

Note :

1.Non-repetitive current pulse 8/20μs exponential decay waveform according to IEC61000-4-5.

2.TLP parameter: Z0=50Ω, tp=100ns, tr=2ns, averaging window from 60ns to 80ns. RDYN is calculated from 4A to 16A.

Curve Characteristics

Fig. 1 - 8 X 20μs Pulse Waveform

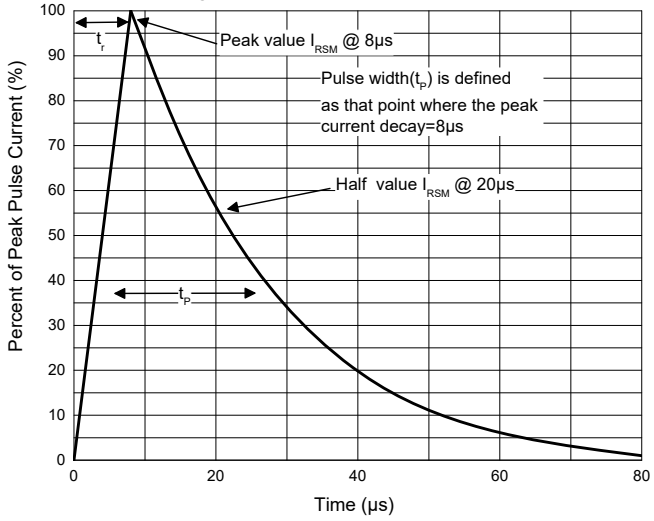


Fig. 2 - Non-Repetitive Peak Pulse Power

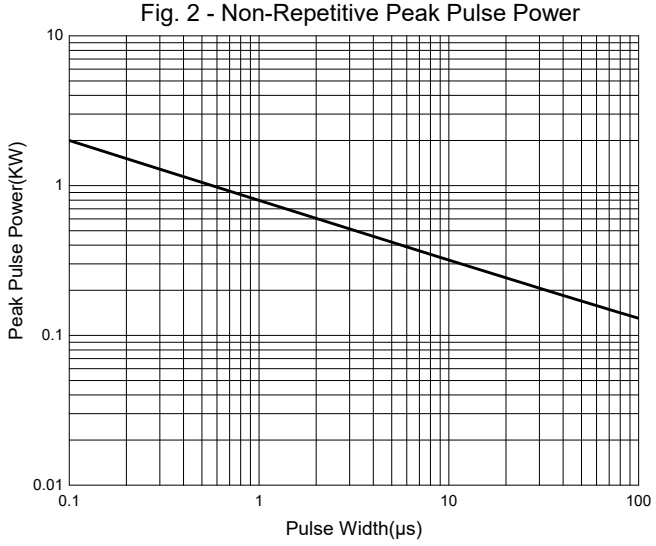


Fig. 3 - Capacitance Characteristics

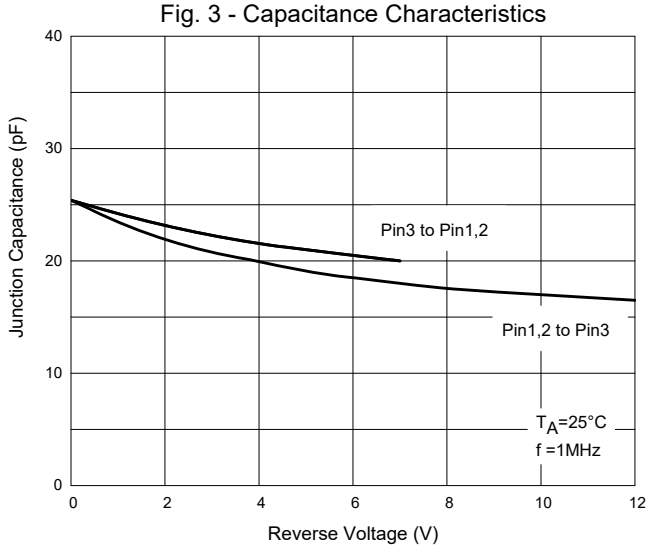


Fig. 4 - Clamping Voltage Characteristics

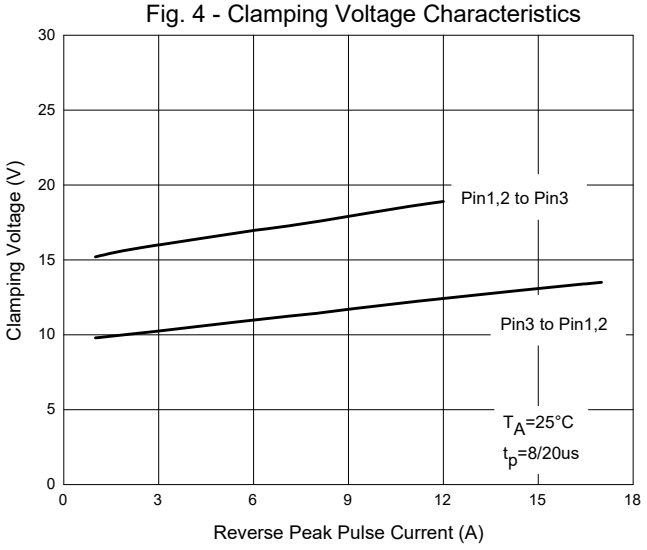


Fig. 5 - TLP Curve

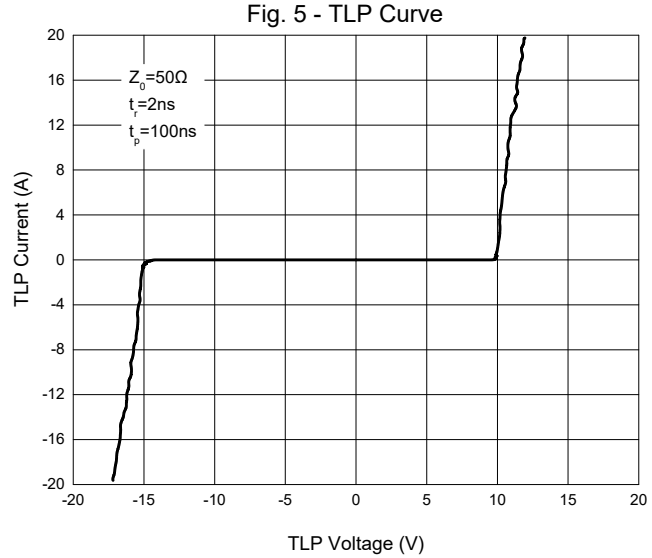
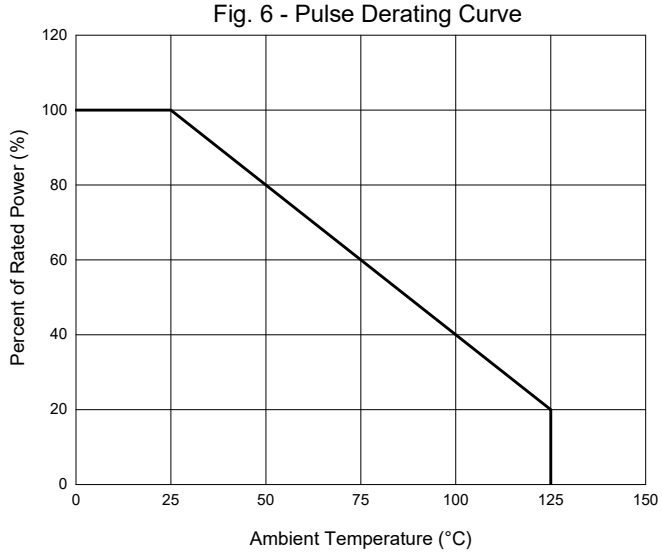


Fig. 6 - Pulse Derating Curve



Ordering Information

Device	Packing
Part Number-TP	Tape&Reel: 3Kpcs/Reel